

December 9, 2003

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Continuation Application of
Serial No.: 10/002,031 11/30/01

YEE-CHIA YEO, CHUN CHIEH LIN, FU-LIANG YANG,
CHEN MING HU

COMPLEMENTARY METAL OXIDE SEMICONDUCTOR
TRANSISTOR TECHNOLOGY USING SELECTIVE
EPITAXY OF A STRAINED SILICON GERMANIUM
LAYER

PRELIMINARY AMENDMENT

Dear Sir:

This is a preliminary amendment for the above referenced Continuation Application.

Please amend the above identified application for patent as follows:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20231, on December 9, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature/Date



12/9/03

TSMC01-1132

October 24, 2003

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: Stephen B. Ackerman, Reg. No. 37,761
28 Davis Ave.
Poughkeepsie, N.Y. 12603

CONTINUATION OF:

Subject: Serial No. 10/002,031

File Date: 11/30/01

Inventor: Y. C. Yeo et al

Examiner: C.W. Lattin

Art Unit: 2812

Title: "COMPLEMENTARY METAL OXIDE SEMICONDUCTOR TRANSISTOR
TECHNOLOGY USING SELECTIVE EPITAXY OF A STRAINED SILICON
GERMANIUM LAYER"

PRELIMINARY AMENDMENT

Dear Sir;

Please enter the attached preliminary amendment, for the above-intended application for patent.

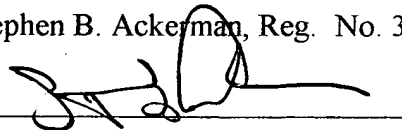
The commissioner is hereby authorized to charge payment of any additional fees involved with added Claims and the like to Deposit Account No. 19-0033

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on Dec. 9, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature



Date 12/9/03